

Sub C1 1 5. (Amended) The interconnection of claim [2] 4, wherein the  
2 aluminum-copper-titanium alloy layer comprises about 0.5 atomic  
3 percent copper and about 0.1 atomic percent titanium.

1 6. (Amended) The interconnection of claim [2] 4, further  
2 comprising:

3 a first titanium layer;

4 a first titanium-nitride layer;

5 a second titanium layer; and

6 a second titanium-nitride layer,

7 wherein the second titanium-nitride layer overlies the second  
8 titanium layer, the aluminum-copper-titanium alloy layer overlies  
9 the second titanium-nitride layer, the first [titanium-nitride]  
10 titanium layer overlies the aluminum-copper-titanium alloy layer,  
11 and the first [titanium] titanium-nitride layer overlies the first  
12 [titanium-nitride] titanium layer.

Sub C2 1 9. (Amended) [The integrated circuit of claim 7,] An  
2 interconnection formed on a substrate of an integrated circuit  
3 comprising an aluminum-copper-titanium alloy layer, wherein the  
4 aluminum-copper-titanium alloy layer contains 0.1 atomic percent  
5 titanium.

1 10. (Amended) The [integrated circuit] interconnection of claim  
2 [7] 2, wherein the aluminum-copper-titanium alloy layer contains  
3 about 0.5% atomic percent copper and about 0.1 atomic percent  
4 titanium.

1 11. (Amended) The [integrated circuit] interconnection of claim  
2 [7] 10, further comprising:  
3 a first titanium layer;  
4 a first titanium-nitride layer;  
5 a second titanium layer; and  
6 a second titanium-nitride layer,  
7 wherein the second titanium-nitride layer overlies the second  
8 titanium layer, the aluminum-copper-titanium alloy layer overlies  
9 the second titanium-nitride layer, the first [titanium-nitride]  
10 titanium layer overlies the aluminum-copper-titanium alloy layer,  
11 and the first [titanium] titanium-nitride layer overlies the first  
12 [titanium-nitride] titanium layer.

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1 14. (Amended) [The integrated circuit of claim 12,] An  
2 integrated circuit comprising:  
3 a substrate; and  
4 an interconnection level disposed about the substrate, the  
5 interconnection level having an aluminum-copper-titanium alloy  
6 layer, wherein the aluminum-copper-titanium alloy layer contains  
7 0.1 atomic percent titanium.

1 15. (Amended) The integrated circuit of claim [12] 14, wherein  
2 the aluminum-copper-titanium alloy layer contains about 0.5%  
3 atomic percent copper and about 0.1 atomic percent titanium.

1 16. (Amended) A multilayered interconnection structure formed on  
2 a substrate, the interconnection comprising:

- 3 a first titanium layer;  
4 a first titanium nitride layer;  
5 an aluminum-copper-[Group IVA metal]titanium alloy layer,  
6 wherein the aluminum-copper-titanium alloy layer contains 0.1  
7 atomic percent titanium;  
8 a second titanium layer; and  
9 a second titanium nitride layer.

1 19. (Amended) The multilayer structure of claim [17] 16, wherein  
2 the aluminum-copper-titanium alloy layer contains 0.1 atomic  
3 percent titanium.

1 21. (Amended) The multilayer structure of claim 16, wherein the  
2 second titanium-nitride layer overlies the second titanium layer,  
3 the aluminum-copper-titanium alloy layer overlies the second  
4 titanium-nitride layer, the first [titanium-nitride] titanium  
5 layer overlies the aluminum-copper-titanium alloy layer, and the  
6 first [titanium] titanium-nitride layer overlies the first  
7 [titanium-nitride] titanium layer.

#### REMARKS

Claims 1-21 were examined. Claims 3-6, 8-11, 13-16 and 21 are amended. Claims 1-3, 7, 8, 12, 13, 17 and 18 are canceled. Claims 4-6, 9-11, 14-16 and 19-21 remain in the application.

The Examiner rejects claims 6, 11 and 21 under 35 U.S.C. §112, first paragraph. The Examiner also rejects claims 1-21 under 35 U.S.C. §102 and §103. Reconsideration of the pending